

Silicon Standard Recovery Diode

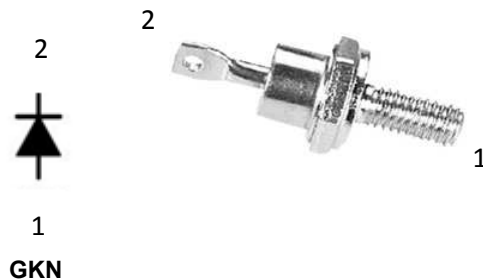
$V_{RRM} = 400\text{ V} - 1600\text{ V}$

$I_F = 25\text{ A}$

Features

- High Surge Capability
- Types up to 1600 V V_{RRM}
- Equivalent to SKN26 Series

DO-4 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified (GKR has leads reversed)

Parameter	Symbol	Conditions	GKN26/04	GKN26/08	GKN26/12	GKN26/14	GKN26/16	Unit
Repetitive peak reverse voltage	V_{RRM}		400	800	1200	1400	1600	V
DC blocking voltage	V_{DC}		400	800	1200	1400	1600	V
Continuous forward current	I_F	$T_C \leq 100\text{ °C}$	25	25	25	25	25	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 10\text{ ms}$	375	375	375	375	375	A
Operating temperature	T_j		-40 to 180	-40 to 180	-40 to 180	-40 to 180	-40 to 180	°C
Storage temperature	T_{stg}		-55 to 180	-55 to 180	-55 to 180	-55 to 180	-55 to 180	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	GKN26/04	GKN26/08	GKN26/12	GKN26/14	GKN26/16	Unit
Diode forward voltage	V_F	$I_F = 60\text{ A}$, $T_j = 25\text{ °C}$	1.55	1.55	1.55	1.55	1.55	V
Reverse current	I_R	$V_R = V_{RRM}$, $T_j = 180\text{ °C}$	4	4	4	4	4	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		2.00	2.00	2.00	2.00	2.00	K/W
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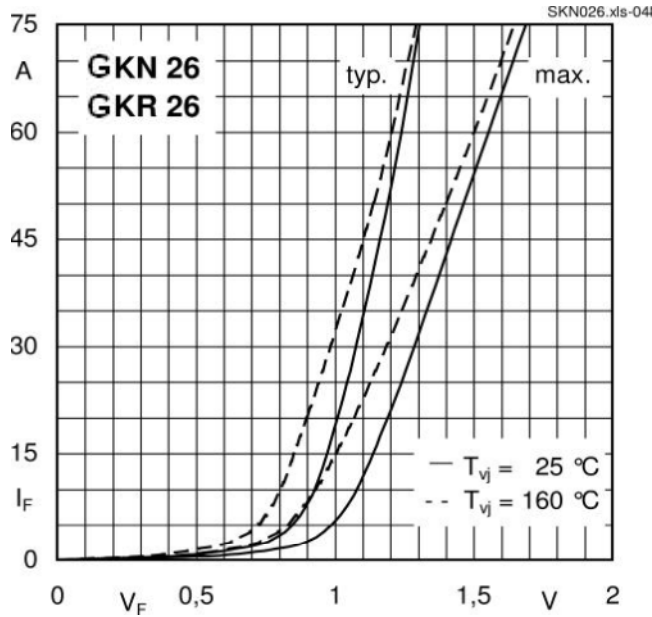


Fig 1: Forward Characteristics

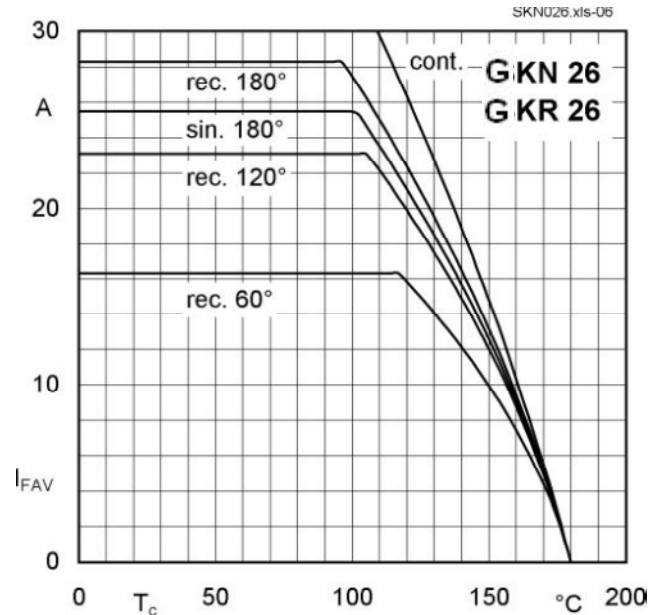


Fig 2: Forward Current vs Case Temp

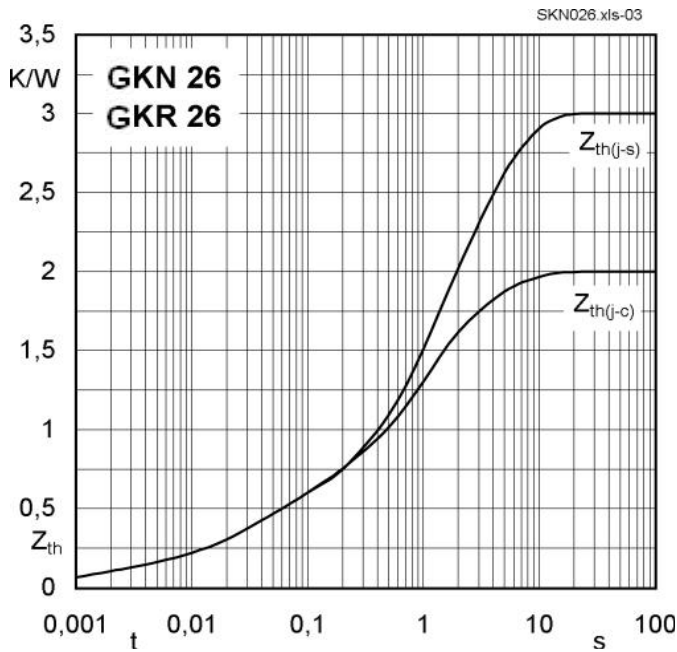


Fig 3: Transient Thermal Impedance vs Time

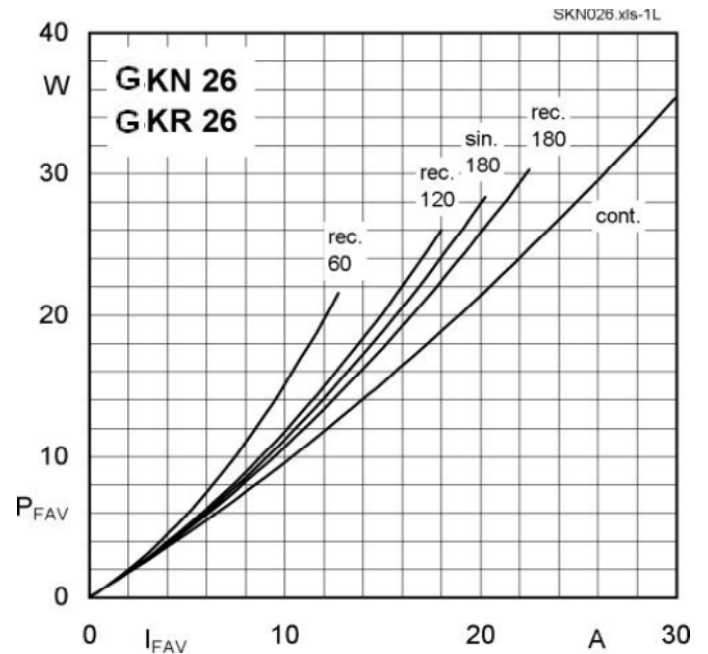


Fig 4: Power Dissipation vs Forward Current